



SIDC07D60E6

Fast switching diode chip in EMCON-Technology

FEATURES:

- 600V EMCON technology 70 µm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip technology is used for:

EUPEC power modules and discrete devices



Applications:

SMPS, resonant applications, drives

Chip Type	V_R	I _F	Die Size	Package	Ordering Code
SIDC07D60E6	600V	15A	2.65 x 2.65 mm ²	sawn on foil	Q67050-A4005- A001

MECHANICAL PARAMETER:

Raster size	2.65 x 2.65				
Area total / active	7.02 / 5.01	mm ²			
Anode pad size	2.17 x 2.17				
Thickness	70	μm			
Wafer size	150	mm			
Flat position	180	deg			
Max. possible chips per wafer	2156 pcs				
Passivation frontside	Photoimide				
Anode metallisation	3200 nm AlSiCu				
Cathode metallisation	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond AI, ≤500μm					
Reject Ink Dot Size	Ø 0.65mm; max 1.2mm				
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



SIDC07D60E6

Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by	,		15	
T_{jmax}	/ _F		15	
Single pulse forward current	I _{FSM}	$t_P = 10 \text{ ms sinusoidal}$	tbd	Α
(depending on wire bond configuration)	1 F S M	tp = 10 ma amadalah	iba	
Maximum repetitive forward current	,		45	
limited by T _{jmax}	I _{FRM}		45	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-55+150	°C

$\textbf{Static Electrical Characteristics} \text{ (tested on chip), } \textit{T}_{j}\text{=25 °C, unless otherwise specified}$

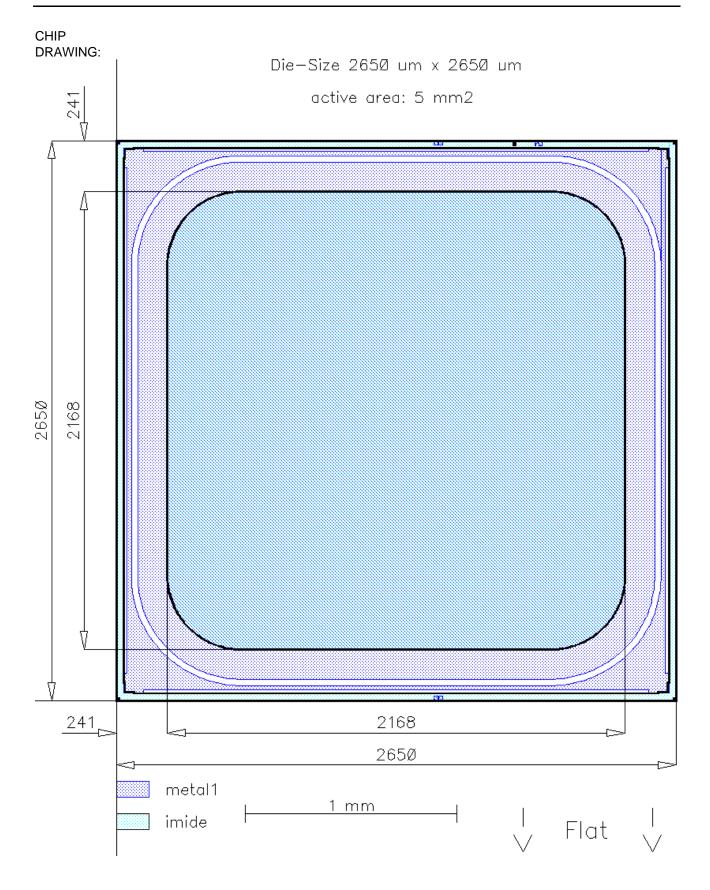
Parameter	Symbol	Cond	Value			Unit	
raiailletei	Syllibol	bol Conditions		min.	typ.	max.	
Reverse leakage current	I_{R}	V _R =600V	<i>T_j</i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V _{Br}	I _R =3mA	<i>T_j</i> =25°C	600			V
Forward voltage drop	V _F	I _F =15A	T _j =25°C		1.25		V

Dynamic Electrical Characteristics, at $T_j = 25$ °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
raiailletei	Syllibol			min.	typ.	max.	
Reverse recovery time	t _{rr1}	I _F =15A	$T_j = 25$ °C		tbd		
	t _{rr2}	$di/dt=600A/ms$ $V_R=300V$	$T_j = 125$ °C				ns
Peak recovery current	I _{RRM1}	di/dt=600A/ms	$T_j = 25$ °C		18.5		_
	I _{RRM2}		$T_j = 125$ °C		21.6		A
Reverse recovery charge	Q _{rr1}	I _F =15A	<i>T_j</i> =25 °C		1.4		
	Q _{rr2}	$di/dt=600A/ms$ $V_R=300V$	T _j =125°C		2.2		μC
Peak rate of fall of reverse recovery current	di _{rr1} /dt	I _F =15A	T _j =25°C		tbd		٥.,
	di _{rr2} /dt	di/dt=600A/ms $V_R=300V$	T _j =125°C				A/μs
Softness	S1	I _F =15A	<i>T_j</i> =25 °C		tbd		1
	S2	$di/dt=600A/ms$ $V_R=300V$	T _j =125°C				'



SIDC07D60E6



Edited by INFINEON Technologies AI PS DD HV3, L 4293M, Edition 1, 2002-01-04



Preliminary

SIDC07D60E6

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet line in the l

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

Published by Infineon Technologies AG Bereich Kommunikation St.-Martin-Strasse 53 D-81541 München © Infineon Technologies AG 2000 All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives world-wide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and / or maintain and sustain and / or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Edited by INFINEON Technologies AI PS DD HV3, L 4293M, Edition 1, 2002-01-04

单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon Technologies(英飞凌)